

NEW ENGLAND SEMICONDUCTOR

BIPOLAR POWER TRANSISTOR NPN PLANAR

PACKAGE	DEVICE TYPE	BV_{CEO} VOLTS	PEAK I_C AMPS	h_{FE} min/max	$I_C @ V_{CE}$ A V	$V_{CE(sat)}$ max VOLTS	$I_C @ I_B$ A A
NPN TO-257 	NSP2880	70	5.0	40-120	1.0/2.0	2.4	5.0/0.5
	NSP3996	80	5.0	40-120	1.0/2.0	0.3	1.0/0.1
	NSP3997	80	5.0	80-240	1.0/2.0	0.3	1.0/0.1
	NSP5660	200	5.0	40-120	0.5/5.0	1.0	2.0/0.4
	NSP5661	300	5.0	25-75	0.5/5.0	1.0	2.0/0.4
	NSP5664	200	10.0	40-120	1.0/5.0	1.2	5.0/1.0
	NSP5665	300	10.0	25-75	1.0/5.0	1.2	5.0/1.0
	NSP5427	80	7.0	30-120	2.0/5.0	0.9	2.0/0.2
	NSP5428	80	7.0	60-240	2.0/5.0	0.9	2.0/0.2
	NSP5429	100	7.0	30-120	2.0/5.0	0.9	2.0/0.2
	NSP5430	100	7.0	60-240	2.0/5.0	0.9	2.0/0.2

PNP PLANAR

PNP TO-257 	NSP3719	40	10.0	25-180	1.0/2.0	0.9	1.5/0.15
	NSP3720	60	10.0	25-180	1.0/2.0	0.9	1.5/0.15
	NSP3867	40	10.0	40-200	1.5/2.0	0.9	1.5/0.15
	NSP3868	60	10.0	30-150	1.5/2.0	0.9	1.5/0.15
	NSP6190	80	5.0	30-120	2.0/0.2	0.9	2.0/0.2
	NSP6191	80	5.0	60-240	2.0/0.2	0.9	2.0/0.2
	NSP6193	100	5.0	60-240	2.0/0.2	0.9	2.0/0.2

• Electrical Characteristics at 25° C unless otherwise noted

^Available in JAN, JANTX, JANTXV